

IR Laser Diode

Application

Industrial use / Biomedical

Property

Wavelength $\lambda = 905\text{nm}$

Output Power = 10mW

Package Type = $\varphi 5.6\text{mm}$

Introduction

Egismos currently markets AlGaAs infrared laser diodes in the 780nm ~ 1550nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer.

Egismos laser diodes are highly rated in a broad range of applications including, but not limited to, laser pointers, green lasers, blue laser DVD, laser barcode scanners, diode laser equipments, medical instruments and aerospace applications.

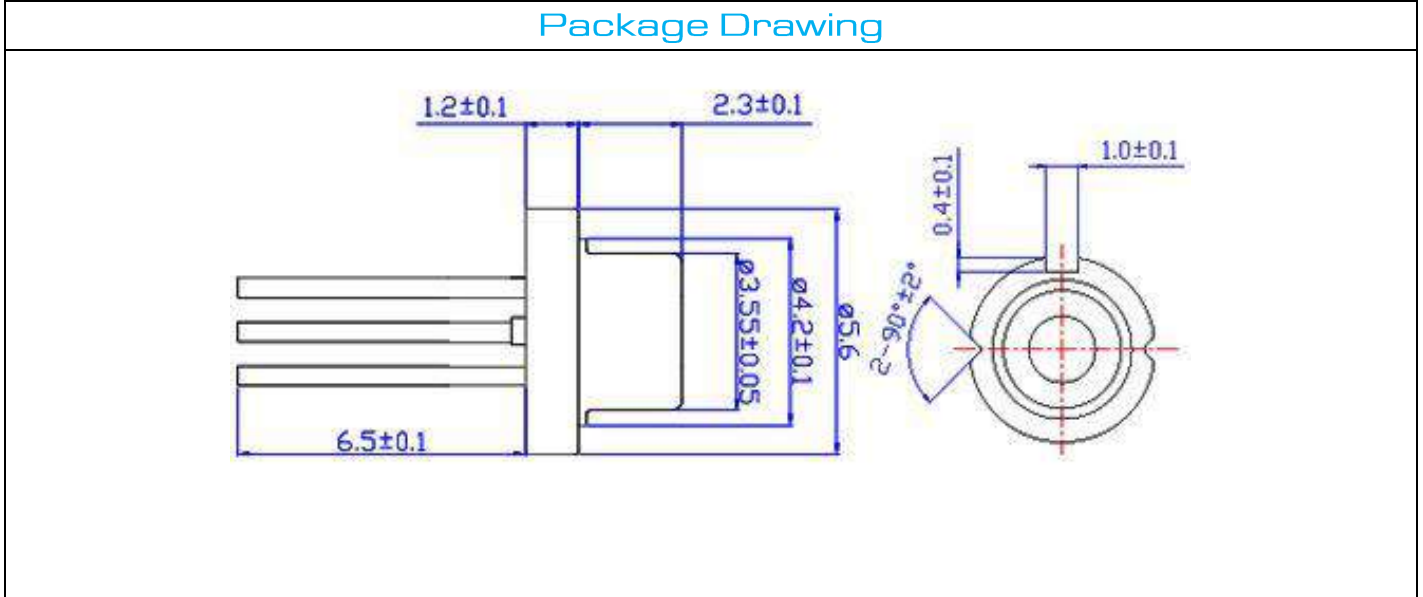
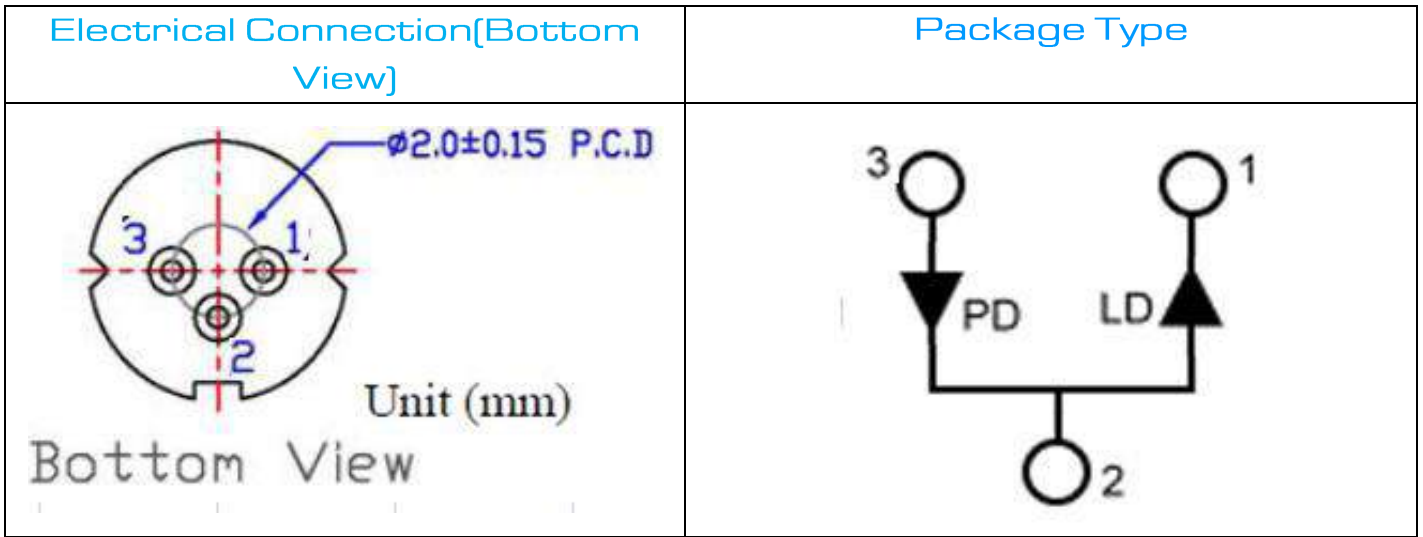


IR Laser Diode Key features

Absolute Maximum Rating at Tc=25°C			
Items	Symbols	Values	Unit
Optical Output Power	Po(CW)	10	mW
Reverse Voltage	V	2	V
Operating Temperature	To	-10~+70	°C
Storage Temperature	Ts	-10~+70	°C

Electrical and Optical Characteristics at Tc=25°C						
Item	Symbols	Min.	Typ.	Max.	Unit	Condition
Optical Output Power	Po	-	-	10	mW	-
Threshold Current	Ith		12	25	mA	-
Operating Current	Iop		35	60	mA	Po=10mW
Operating Voltage	Vop	1.5	1.8	2.3	V	Po=10mW
Peak Wavelength	λ_p	885	905	915	nm	Po=10mW

Beam Divergence	$\theta_{//}$	7	10	15	deg	Po=10mW
	θ_{\perp}	25	35	38	deg	Po=10mW



Specifications are subject to change without notice.

